Title (en)

A semiconductor memory device with information loss self-detect capability

Title (de)

Halbleiterspeicheranordnung mit Fähigkeit zur Informationsverlusterkennung

Title (fr)

Dispositif de mémoire à semi-conducteurs avec la capacité de détection de perte d'information

Publication

EP 1717817 B8 20160518 (EN)

Application

EP 05103557 A 20050429

Priority

EP 05103557 A 20050429

Abstract (en)

[origin: EP1717817A1] A semiconductor memory device (100), including a plurality of programmable memory cells (MC) each one adapted to be brought into one among at least a first status and a second status, said plurality of memory cells including memory cells intended to store data, and means for accessing (115,130,135) the memory cells for reading/modifying their status. At least one memory cell (FMC) in said plurality is used as detector memory cell, and control means (145) operatively associated with the at least one detector memory cell are provided, said control means being adapted to establishing a potential loss of the data stored in the memory cells of said plurality based on a detected first status of the at least one detector memory cell.

IPC 8 full level

G11C 13/00 (2006.01); **G11C 16/34** (2006.01)

CPC (source: EP)

G11C 11/22 (2013.01); **G11C 11/2275** (2013.01); **G11C 13/0004** (2013.01); **G11C 13/0033** (2013.01); **G11C 13/0069** (2013.01); **G11C 16/3431** (2013.01); G11C 2013/0083 (2013.01)

Cited by

EP1927990A3; EP1933327A3; EP1858021A3; CN102369579A; US7539050B2; US7460394B2; US10319437B2; JP2008152904A; WO2007145710A1; WO2010076826A1; WO2019059970A1

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

EP 1717817 A1 20061102; **EP 1717817 B1 20160413**; **EP 1717817 B8 20160518**; US 2007253238 A1 20071101; US 7414902 B2 20080819

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EP 05103557 A 20050429; US 41587906 A 20060501